

# SANYO Semiconductors DATA SHEET



## **Bi-CMOS LSI** LV8411GR — For DSC, and Cell Phone Camera Modules 4-channel Single-chip Motor Driver IC

#### **Overview**

The LV8411GR is an H bridge motor driver IC and is able to control 4 modes of forward, reverse, brake, and standby. This IC housed in a miniature package is optimum for use in a stepping motor driving system for DSC or a camera module of cell phones.

#### Features

- Saturation drive H bridge: 4 channels
- Built-in thermal protection circuit
- Built-in low voltage malfunction prevention circuit
- Incorporates a transistor for driving photosensors

#### **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Power supply voltage 1	V <sub>M</sub> max		6.0	V
Power supply voltage 2	V <sub>CC</sub> max		6.0	V
Output peak current	I <sub>O</sub> peak	Channels 1 to 4, t $\leq$ 10msec, ON-duty $\leq$ 20%	600	mA
Output continuous current 1	I <sub>O</sub> max1	Channels 1 to 4	400	mA
Output continuous current 2	I <sub>O</sub> max2	PI1	30	mA
Allowable power dissipation	Pd max	Mounted on a circuit board*	1.05	W
Operating temperature	Topr		-30 to +85	°C
Storage temperature	Tstg		-55 to +150	°C

\* Specified circuit board : 40mm×50mm×0.8mm : glass epoxy four-layer board

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## LV8411GR

### Recommended Operating Conditions at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Power supply voltage range 1	VM		2.5 to 5.5	V
Power supply voltage range 2	VCC		2.5 to 5.5	V
Logic input voltage range	V <sub>IN</sub>		0 to V <sub>CC</sub> +0.3	V
Input frequency	fIN	IN1 to 8, INA	to 100	kHz

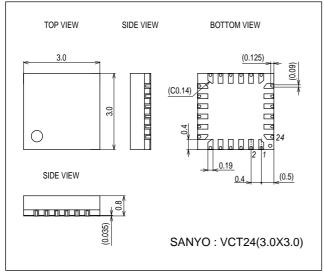
## **Electrical Characteristics** at Ta = 25°C, $V_M$ = 5V, $V_{CC}$ = 3.3V, unless otherwise specified.

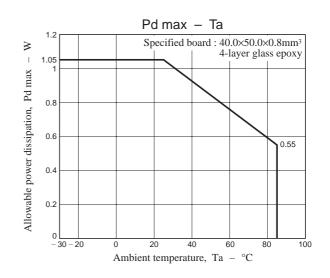
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Parameter	Symbol	Conditions		Ratings		Unit
Falameter	Symbol	mi		typ	max	Unit
Standby mode current drain	Istn	IN1 to 8 = "L"			1.0	μA
VM current drain	IM	IN1 = "H", IM1 + IM2, with no load	50	100	200	μA
V <sub>CC</sub> current drain	ICC	IN1 = "H"	0.3	0.6	1.2	mA
$V_{CC}$ low-voltage cutoff voltage	VthV <sub>CC</sub>		2.0	2.25	2.5	V
Low-voltage hysteresis voltage	VthHIS		100	150	200	mV
Thermal shutdown temperature	TSD	Design guarantee value *	160	180	200	°C
Thermal hysteresis width	ΔTSD	Design guarantee value *	10	30	50	°C
OUT1 to 8	•			•		
Logic pin internal pull-down resistance	Rin	IN1 to 8	50	100	200	kΩ
Logic pin input current	linL	V <sub>IN</sub> = 0V, IN1 to 8			1.0	μΑ
	linH	V <sub>IN</sub> = 3.3V, IN1 to 8	16.5	33	60	μΑ
Logic input high-level voltage	Vinh	IN1 to 8	2.5			V
Logic input low-level voltage	Vinl	IN1 to 8			1.0	V
Output on-resistance	Ronu	I <sub>O</sub> = 400mA, upper ON resistance		0.75	0.9	Ω
	Rond	I <sub>O</sub> = 400mA, lower ON resistance		0.45	0.6	Ω
Output leakage current	lOleak				1.0	μA
Diode forward voltage	VD	ID = -400mA	0.7	0.9	1.2	V
PI1	•			•		
Logic pin internal pull-down resistance	Rin	INA	50	100	200	kΩ
Logic pin input current	linL	V <sub>IN</sub> = 0V, INA			1.0	μA
	linH	V <sub>IN</sub> = 3.3V, INA	16.5	33	60	μA
Logic input high-level voltage	Vinh	INA	2.5			V
Logic input low-level voltage	Vinl	INA		1.0	V	
Output on-resistance	Ron	I <sub>O</sub> = 10mA		3.0	6.0	Ω
Output leakage current	lOleak				1.0	μA

### **Package Dimensions**

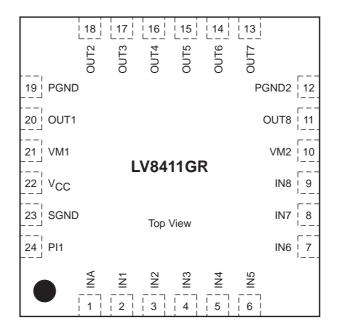
unit : mm (typ)



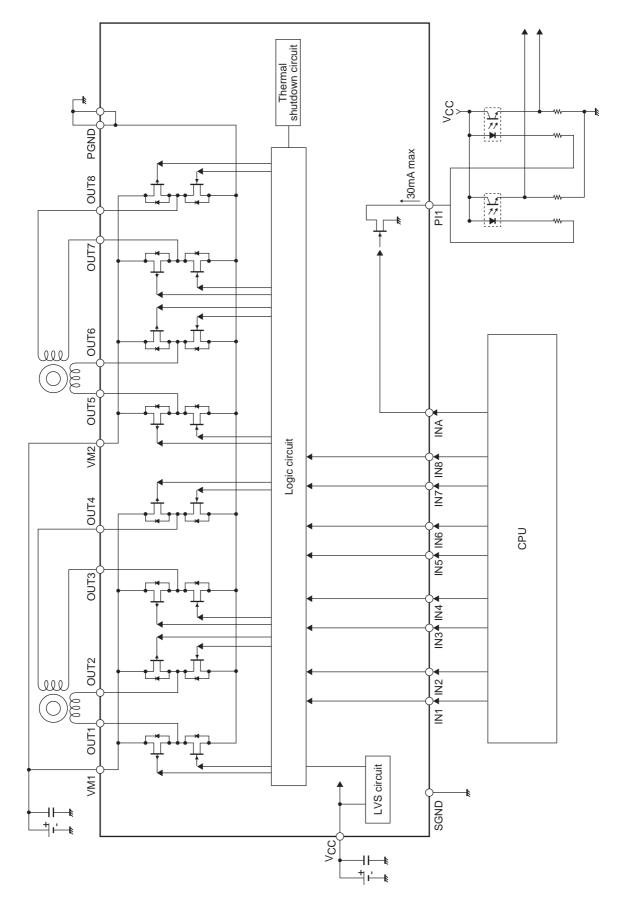




## **Pin Assignment**



## **Block Diagram**



### **Pin Functions**

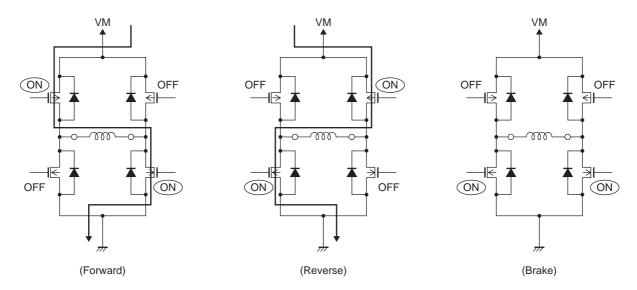
Pin No.	Pin name	Pin Function	Equivalent Circuit
1	INA	Control signal input pin	
		(Photo sensor driving transistor)	
2	IN1	Control signal input pin	
3	IN2	Control signal input pin	
4	IN3	Control signal input pin	
5	IN4	Control signal input pin	
			★   +
6	IN5	Control signal input pin	
7	IN6	Control signal input pin	
8	IN7	Control signal input pin	10kΩ
9	IN8	Control signal input pin	
			●
			<b>▲ ≧</b> 100kΩ <b>→</b>
			CND
			GND
		<u>                                     </u>	
11	OUT8	Outpin	
13	OUT7	Outpin	VM
14	OUT6	Outpin	Ŷ
15	OUT5	Outpin	
15 16	OUT4	Outpin	
17	OUT3	Outpin	
18	OUT2	Outpin	
20	OUT1	Outpin	
			•( )
			<
			•
			PGND
24	PI1	Photo sensor driving transistor output	$\sim$
		pin	• ( )
			GND
22	V <sub>CC</sub>	Logic system power supply	
		connection pin	
10	VM2	Motor power supply connection pin	
21	VM2 VM1	Motor power supply connection pin	
	SGND		
23		Signal ground	
12	PGND2	Power ground	
19	PGND1	Power ground	

#### Logic input specifications

• Common channels 1 to 4 ch1 : IN1 to IN2, OUT1 to OUT2 ch2 : IN3 to IN4, OUT3 to OUT4 ch3 : IN5 to IN6, OUT5 to OUT6 ch4 : IN7 to IN8, OUT7 to OUT8

Input		Output		On another mode	
IN1	IN2	OUT1	OUT2	Operation mode	
L	L	OFF	OFF	Standby	
н	L	н	L	CW (forward)	
L	н	L	н	CCW (reverse)	
н	н	L	L	Brake	

• Output stage transistor function



• Photo sensor driving transistor

When thermal shutdown and V<sub>CC</sub> low-voltage cut circuits are activated, OUT1 through OUT8 are turned OFF under control of the internal circuit. But the output (PI1) of photo sensor driving transistor continues operation.

Input	Photo sensor driving
INA	PI1
L	OFF
Н	ON

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